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Yamamoto

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(54) **CRYSTALLINE TURBOSTRATIC BORON NITRIDE POWDER AND METHOD FOR PRODUCING SAME**

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(\*) Notice: Subject to any disclaimer, the term of this patent is extended or adjusted under 35 U.S.C. 154(b) by 0 days.

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(51) Int. Cl.<sup>7</sup> ..... **C01B 21/064**

(52) U.S. Cl. .... **423/290; 428/403**

(58) Field of Search ..... **423/290**

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(57) **ABSTRACT**

Turbostratic boron nitride (t-BN) powder having excellent sinterability. A mixture of boric acid anhydride and urea is charged in a reaction vessel together with alkali-borate, heated step by step in the vessel in a nonoxidizing gas atmosphere of one atmospheric pressure or above, and kept at a temperature from 850° C. to 950° C. to yield an intermediate product formal substantially of an amorphous boron nitride powder (first reaction step). Then the intermediate product is heated and kept at a temperature from 1200° C. to 1400° C. to crystallize crystalline t-BN, and the product is purified by washing with water and aqueous solution to obtain pure crystalline t-BN powder.

**6 Claims, 8 Drawing Sheets**

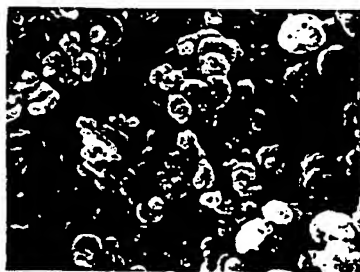
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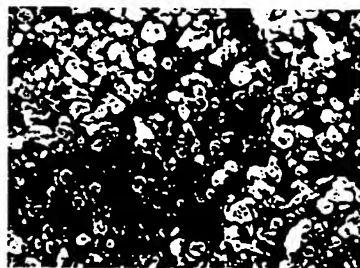
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